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FDP20N50 / FDPF20N50 / FDPF20N50T N-Channel UniFETTM MOSFET

500 V, 20 A, 230 m Ω

Features

- + $R_{DS(on)}$ = 200 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 10 A
- Low Gate Charge (Typ. 45.6 nC)
- Low C_{rss} (Typ. 27 pF)
- 100% Avalanche Tested

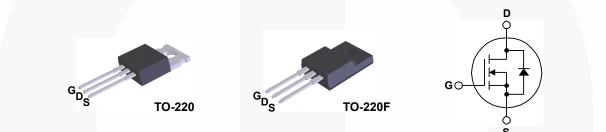
Applications

- LCD/LED/PDP TV
- Lighting
- Uninterruptible Power Supply
- AC-DC Power Supply

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.

November 2013



Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

	Parameter		FDP20N50	FDPF20N50 / FDPF20N50T	Unit
Drain-Source Voltage			500		
Drain Current - Continuous (T _C = 25°C) - Continuous (T _C = 100°C)			20 12.9	20 * 12.9 *	A A
Drain Current -	Pulsed	(Note 1)	80	80 *	А
Gate-Source voltage			±30		V
Single Pulsed Avalanche Energy (No			1110		
Avalanche Current		(Note 1)	20		А
Repetitive Avalanche Energy (Note 1)		(Note 1)	25		mJ
Peak Diode Recovery dv/dt (Note 3)		(Note 3)	4.5		V/ns
	•		250 2.0	38.5 0.3	W W/°C
Operating and Storage Temperature Range			-55 to +150		°C
Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			300		°C
	Drain Current - Drain Current - Drain Current - Gate-Source voltage Single Pulsed Avalanche Avalanche Current Repetitive Avalanche Er Peak Diode Recovery de Power Dissipation (Operating and Storage 1 Maximum Lead Tempera	Drain-Source VoltageDrain Current- Continuous ($T_C = 25^{\circ}C$) - Continuous ($T_C = 100^{\circ}C$)Drain Current- PulsedGate-Source voltageSingle Pulsed Avalanche EnergyAvalanche CurrentRepetitive Avalanche EnergyPeak Diode Recovery dv/dtPower Dissipation ($T_C = 25^{\circ}C$) - Derate above $25^{\circ}C$ Operating and Storage Temperature RangeMaximum Lead Temperature for Soldering,	Drain-Source Voltage Drain Current - Continuous ($T_C = 25^{\circ}C$) - Continuous ($T_C = 100^{\circ}C$) Drain Current - Pulsed (Note 1) Gate-Source voltage Single Pulsed Avalanche Energy Avalanche Current (Note 1) Repetitive Avalanche Energy (Note 1) Peak Diode Recovery dv/dt Power Dissipation ($T_C = 25^{\circ}C$) - Derate above $25^{\circ}C$ Operating and Storage Temperature Range Maximum Lead Temperature for Soldering,	Drain-Source Voltage5Drain Current- Continuous ($T_C = 25^{\circ}C$) - Continuous ($T_C = 100^{\circ}C$)20 12.9Drain Current- Pulsed(Note 1)Gate-Source voltage \pm Single Pulsed Avalanche Energy(Note 2)Avalanche Current(Note 1)Repetitive Avalanche Energy(Note 1)Peak Diode Recovery dv/dt(Note 3)Power Dissipation($T_C = 25^{\circ}C$) - Derate above $25^{\circ}C$ 250 2.0Operating and Storage Temperature Range-55 toMaximum Lead Temperature for Soldering,-20	ParameterFDP20N50FDPF20N50TDrain-Source Voltage 500 Drain Current- Continuous (T _C = 25°C) - Continuous (T _C = 100°C)20 12.920* 12.9*Drain Current- Pulsed(Note 1)8080*Gate-Source voltage ± 30 Single Pulsed Avalanche Energy1110Avalanche Current(Note 1)20Repetitive Avalanche Energy(Note 1)20Repetitive Avalanche Energy(Note 1)25Peak Diode Recovery dv/dt(Note 3)4.5Power Dissipation(T _C = 25°C) - Derate above 25°C250 2.038.5 0.3Operating and Storage Temperature Range-55 to +150Maximum Lead Temperature for Soldering,300

Thermal Characteristics

Symbol	Parameter	FDP20N50	FDPF20N50/ FDPF20N50T	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.5	3.3	°C/W	
R _{0JA} Thermal Resistance, Junction-to-Ambient, Max.		62.5	62.5	_ 0/10	

Part Nu	umber	Top Mark	Package	Packing Method	Reel Size	Ta	ape Width	n Qu	antity	
FDP2	0N50	FDP20N50	TO-220	Tube	N/A		N/A	50	units	
FDPF20N50 FDPF20N50		TO-220F	TO-220F Tube N/A		N/A		50 units			
FDPF2	0N50T	FDPF20N50	TO-220F	Tube	N/A	N/A		50	50 units	
Electric	al Char	racteristics T _c = 25	°C unless ot	herwise noted.						
Symbol		Parameter		Conditions		Min.	Тур.	Max.	Unit	
Off Charac	teristics									
BV _{DSS}	Drain-Sou	irce Breakdown Voltage	V _{GS} =	V _{GS} = 0 V, I _D = 250 μA		500			V	
ΔBV_{DSS} / ΔT_{J}	Breakdow Coefficien	n Voltage Temperature t	I _D = 25	I_D = 250 µA, Referenced to 25°C			0.5		V/°C	
I _{DSS}	Zero Gate	e Voltage Drain Current		$V_{DS} = 500 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 400 \text{ V}, T_{C} = 125^{\circ}\text{C}$				1 10	μΑ μΑ	
I _{GSSF}	Gate-Bod	y Leakage Current, Forwar	d V _{GS} = :	30 V, V _{DS} = 0 V				100	nA	
I _{GSSR}	Gate-Bod	y Leakage Current, Revers	e V _{GS} = ·	-30 V, V _{DS} = 0 V				-100	nA	
On Charac	teristics						•			
V _{GS(th)}	Gate Threshold Voltage		V _{DS} = V	√ _{GS} , I _D = 250 μA		3.0		5.0	V	
R _{DS(on)}	Static Drain-Source On-Resistance		V _{GS} =	V _{GS} = 10 V, I _D = 10 A			0.20	0.23	Ω	
9 _{FS}	Forward Transconductance		V _{DS} = 4	40 V, I _D = 10 A			24.6		S	
Dynamic C	haracteris	tics					•			
C _{iss}	Input Capacitance			V _{DS} = 25 V, V _{GS} = 0 V,			2400	3120	pF	
C _{oss}	Output Ca	apacitance	f = 1.0	f = 1.0 MHz			355	465	pF	
C _{rss}	Reverse Transfer Capacitance						27		pF	
Switching	Characteri	stics								
t _{d(on)}	Turn-On Delay Time			V _{DD} = 250 V, I _D = 20 A,			95	200	ns	
t _r	Turn-On F	Rise Time	V _{GS} =	$V_{\rm GS}$ = 10 V, R _G = 25 Ω			375	760	ns	
t _{d(off)}	Turn-Off D	Delay Time					100	210	ns	
t _f	Turn-Off F	all Time			(Note 4)		105	220	ns	
Qg	Total Gate	e Charge		V _{DS} = 400 V, I _D = 20 A,			45.6	59.5	nC	
Q _{gs}	Gate-Sou	-Source Charge		V _{GS} = 10 V			14.8		nC	
Q _{gd}	Gate-Drai	n Charge		(Note 4)			21.6		nC	
	rce Diode O	Characteristics and Maxir	num Rating	s						
I _S Maximum Continuous Drain-Source Dio		Diode Forwa	rd Current				20	А		
I _{SM}	Maximum	Pulsed Drain-Source Diod	e Forward C	urrent				80	А	
V _{SD}	Drain-Sou	rce Diode Forward Voltage	e V _{GS} = (V _{GS} = 0 V, I _S = 20 A				1.4	V	
t _{rr}	Reverse F	Recovery Time		0 V, I _S = 20 A,			507		ns	
Q _{rr}	Reverse F	Recovery Charge	dl _F /dt =	:100 A/μs			7.20		μC	

FDP20N50 / FDPF20N50 / FDPF20N50T — N-Channel UniFETTM MOSFET

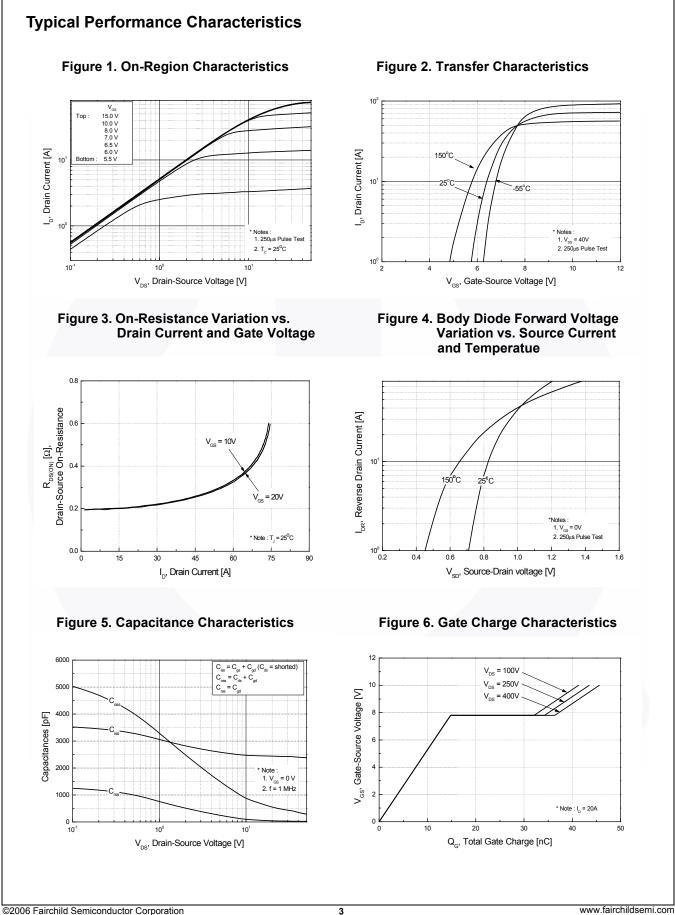
Notes:

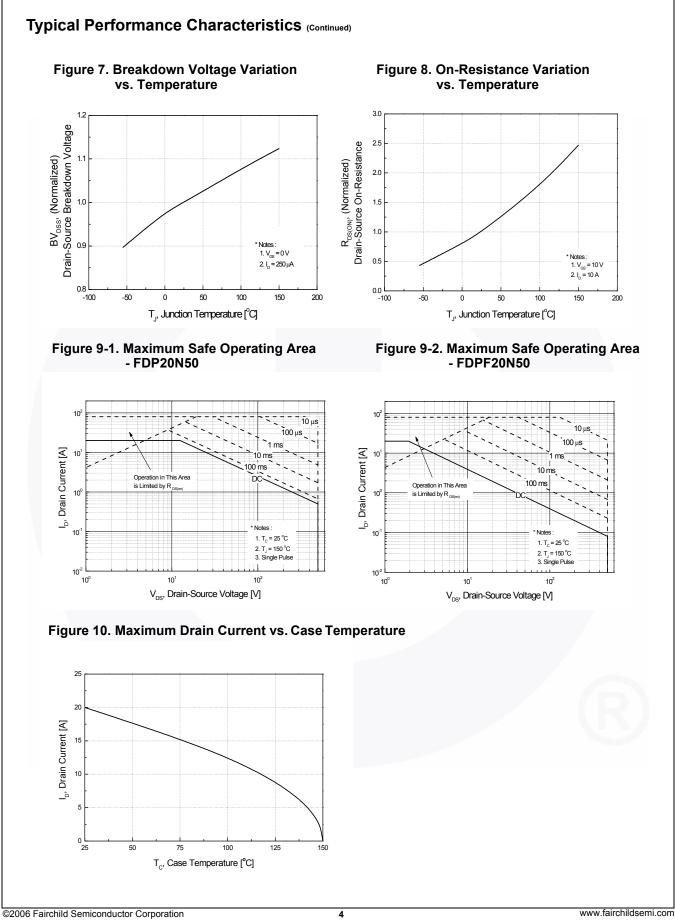
1. Repetitive rating: pulse-width limited by maximum junction temperature.

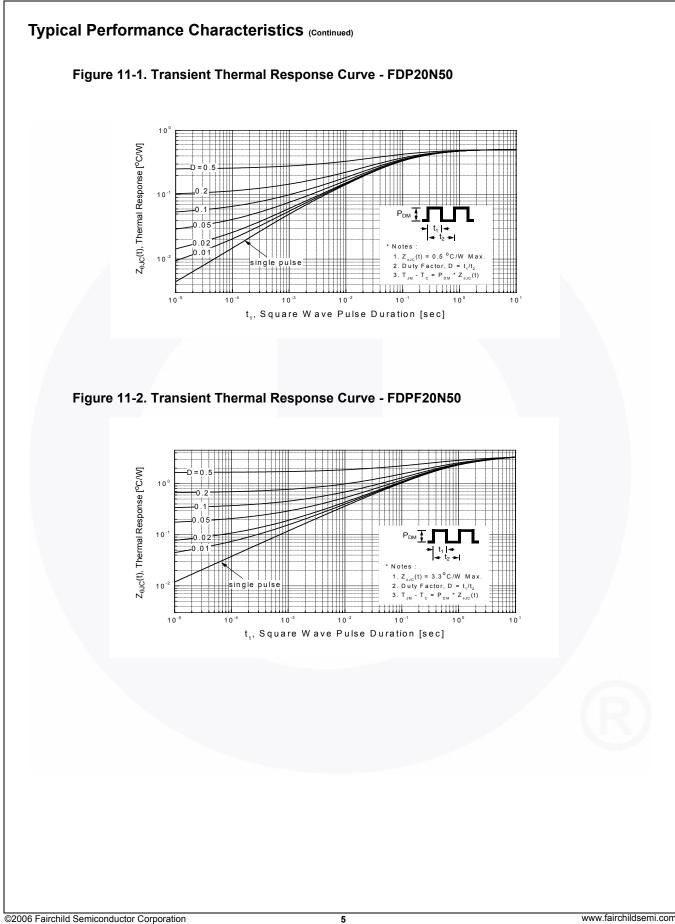
2. L = 5.0 mH, I_{AS} = 20 A, V_{DD} = 50 V, R_G = 25 $\Omega,$ starting T_J = 25°C.

3. I_{SD} \leq 20 A, di/dt \leq 200 A/µs, V_{DD} \leq BV_{DSS}, starting T_J = 25°C.

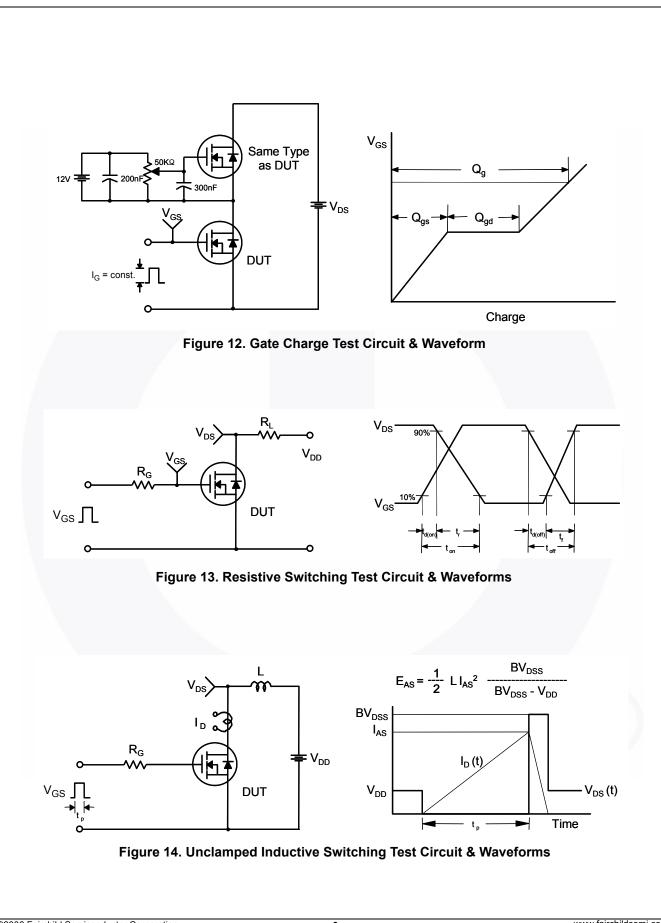
4. Essentially independent of operating temperature typical characteristics.



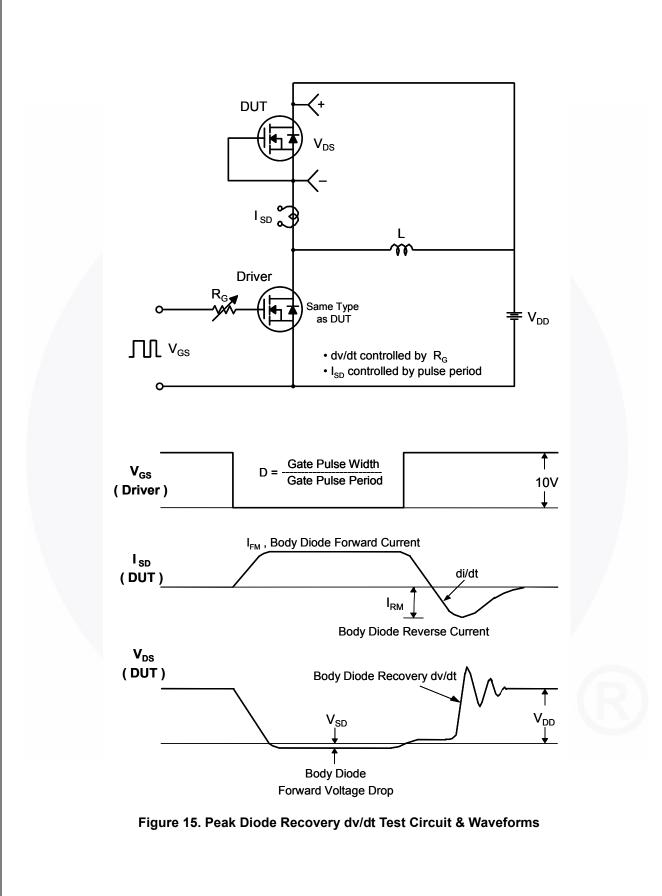


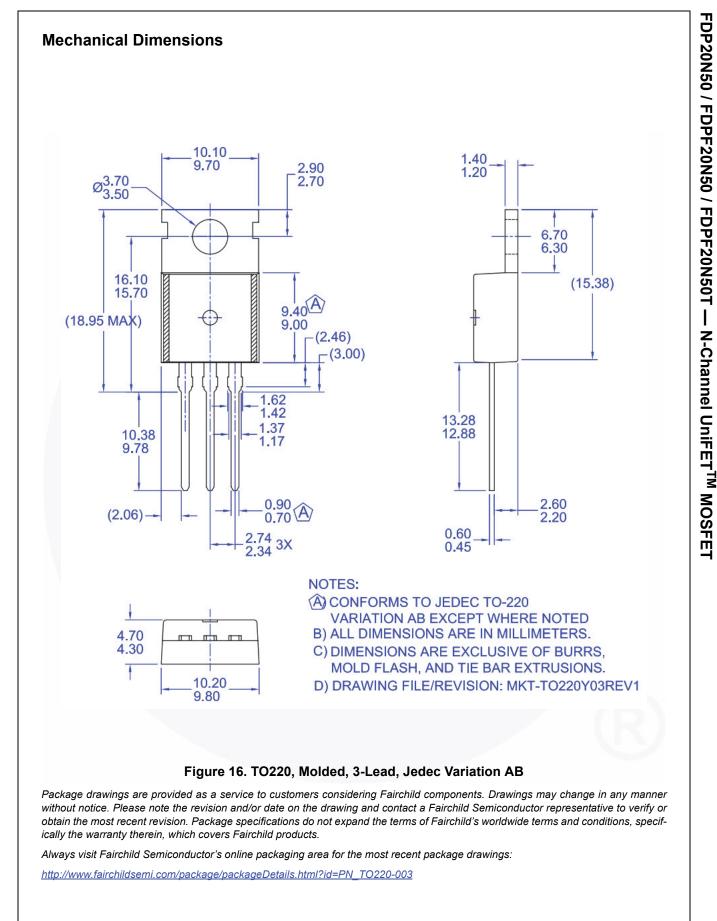


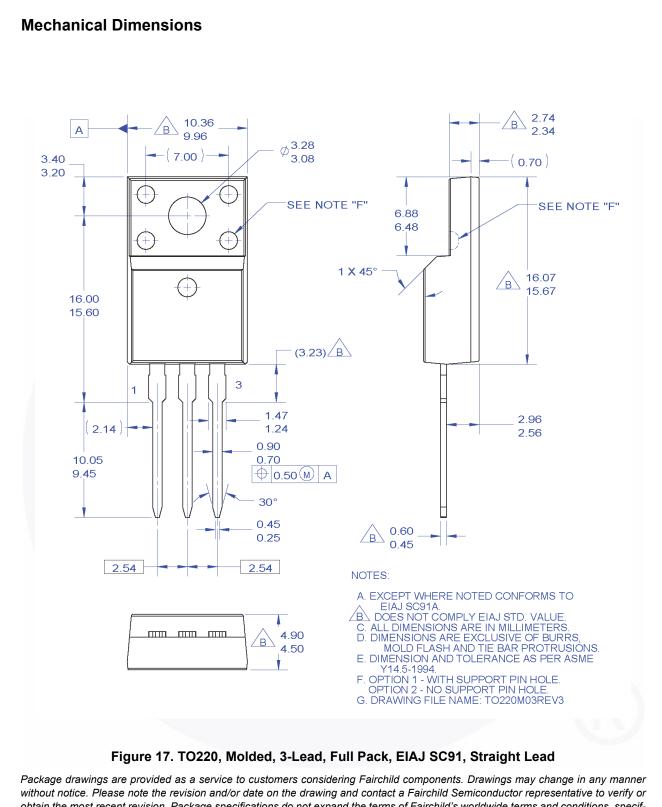
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6







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